

In re Patent Application of:  
**HILL**  
Serial No. 10/761,338  
Filed: JANUARY 22, 2004

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IN THE DESCRIPTION

Please replace the paragraph extending from Page 11,  
lines 15 to Page 12, line 6 with:

Applicants U.S. provisional application 60/441,413  
~~<attorney docket 50422-1>~~ entitled "Preparation of type IV  
Semiconductor Nanocrystals Doped with Rare-earth Ions and  
Product Thereof" filed January 22, 2003 teaches methods of  
preparing group IV semiconductor nanocrystals doped with rare-  
earth ions. In one embodiment provided in that application,  
the invention provides a doped type IV semiconductor  
nanocrystal layer. In another aspect, the invention provides  
a doped type IV semiconductor nanocrystal powder comprising  
crystals of a group IV element that bear on their surface  
atoms of one or more rare earth elements. The powder can also  
be used to form a layer, for example by including the powder  
in a layer of a dielectric medium for example spun glass, or a  
polymer. That application is incorporated herein in its  
entirety by reference. Two regular U.S. applications  
10/761,275 and 10/761,409 ~~<attorney dockets 50422-7; 50422-8~~  
> based on the above provisional have been filed the same day  
as this application and are hereby incorporated by reference  
in their entirety. In the entire description that follows,  
whenever a rare-earth doped group IV semiconductor nanocrystal  
material (REDGIVN material) is referred to, any material  
taught in the incorporated documents is contemplated.